Amendment to the Claims:

This listing of claims replaces all prior versions, and listings, of claims in the application:

1. (Previously Presented): A method comprising:
 generating alignment light to align a wafer with an imaging
plate of an optical system;

modifying the alignment light using an alignment grating on the imaging plate, the alignment grating having a first pitch, wherein said modifying the alignment light using an alignment grating comprises reflecting light from the alignment grating; and

further modifying the alignment light at a pupil plane of the optical system to have an intensity periodicity of less than the first pitch at a wafer plane.

- 2. (Original): The method of claim 1, wherein the intensity periodicity of the alignment light at the wafer plane is equal to half the first pitch.
 - 3-4. (Canceled).
 - 5. (Original): The method of claim 1, further comprising:

reflecting a reflected portion of the alignment light from an alignment pattern on a wafer at the wafer plane, the alignment pattern having a second pitch less than the first pitch.

- 6. (Original): The method of claim 5, wherein the second pitch is half the first pitch.
- 7. (Original): The method of claim 5, further comprising: receiving at least a portion of the reflected portion of the light in a detector; and

determining an alignment characteristic based on the receiving.

- 8. (Original): The method of claim 7, further comprising changing the position of the wafer based on the alignment characteristic.
- 9. (Original): The method of claim 7, further comprising determining an alignment position based on the alignment characteristic.

- 10. (Original): The method of claim 9, wherein changing the position of the wafer based on the alignment characteristic comprises positioning the wafer at the alignment position.
- 11. (Original): The method of claim 1, wherein further modifying the alignment light at the pupil plane comprises:

blocking a central maximum of the alignment light at the pupil plane; and

allowing unblocked light including a first order maximum of the alignment light to pass at the pupil plane.

- 12. (Canceled).
- 13. (Currently Amended): The method of claim 1[[2]], further comprising:

generating patterning light to pattern one or more devices on the wafer;

modifying the patterning light using a device pattern on the imaging plate; and

exposing a portion of a resist layer on the wafer using the patterning light.

14-46. (Canceled)

47. (New): An apparatus comprising:

means for generating alignment light to align a wafer with an imaging plate of an optical system;

means for modifying the alignment light using an alignment grating on the imaging plate comprising means for reflecting light from the alignment grating, the alignment grating having a first pitch; and

means for further modifying the alignment light at a pupil plane of the optical system to have an intensity periodicity of less than the first pitch at a wafer plane.

- 48. (New): The apparatus of claim 47, wherein the intensity periodicity of the alignment light at the wafer plane is equal to half the first pitch.
- 49. (New): The apparatus of claim 47, further comprising:
 means for reflecting a reflected portion of the alignment
 light from an alignment pattern on a wafer at the wafer plane,
 the alignment pattern having a second pitch less than the
 first pitch.
- 50. (New): The apparatus of claim 49, wherein the second pitch is half the first pitch.

51. (New): The method of claim 49, further comprising: means for receiving at least a portion of the reflected portion of the light in a detector; and

means for determining an alignment characteristic based on the receiving.

- 52. (New): The apparatus of claim 51, further comprising means for changing the position of the wafer based on the alignment characteristic.
- 53. (New): The apparatus of claim 51, further comprising means for determining an alignment position based on the , alignment characteristic.
 - 54. (New): The apparatus of claim 52, wherein said means for changing the position of the wafer based on the alignment characteristic comprises means for positioning the wafer at the alignment position.
 - 55. (New): The apparatus of claim 47, wherein said means for further modifying the alignment light at the pupil plane comprises:

means for blocking a central maximum of the alignment light at the pupil plane; and

means for allowing unblocked light including a first order maximum of the alignment light to pass at the pupil plane.

56. (New): The apparatus of claim 47, further comprising: means for generating patterning light to pattern one or more devices on the wafer;

means for modifying the patterning light using a device pattern on the imaging plate; and

means for exposing a portion of a resist layer on the wafer using the patterning light.